



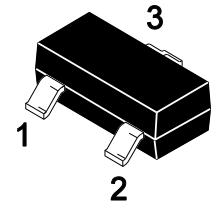
MMBD7000[®]

Silicon Epitaxial Planar Switching Diode

Features

- Dual Switching Diode
- Fast Switching Speed

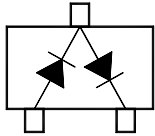
Package



1. Anode1 2. Cathode2
3. Cathode1, Anode2

Equivalent Circuit

3. Cathode1, Anode2



1. Anode1 2. Cathode2

Marking Code : B7

Electrical Characteristics (at $T_J = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-Repetitive Peak Forward Surge Current at $t=10\text{ms}$	I_{FSM}	2	A
Maximum Power Dissipation	P_D	350	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-50 to +150	$^\circ\text{C}$

Electrical Characteristics (at $T_J = 25^\circ\text{C}$)

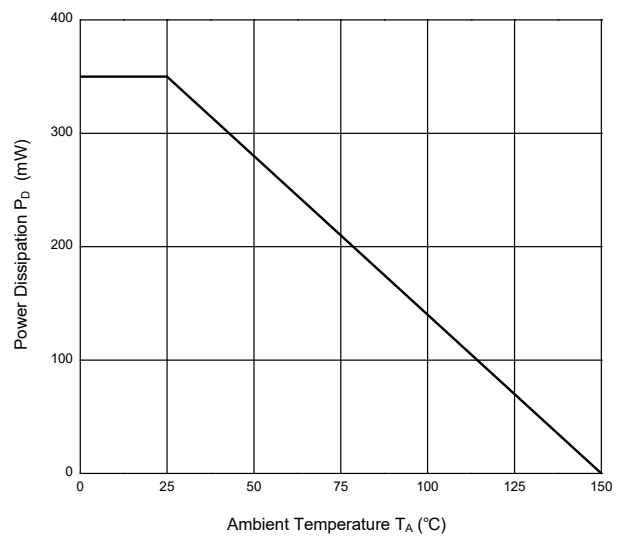
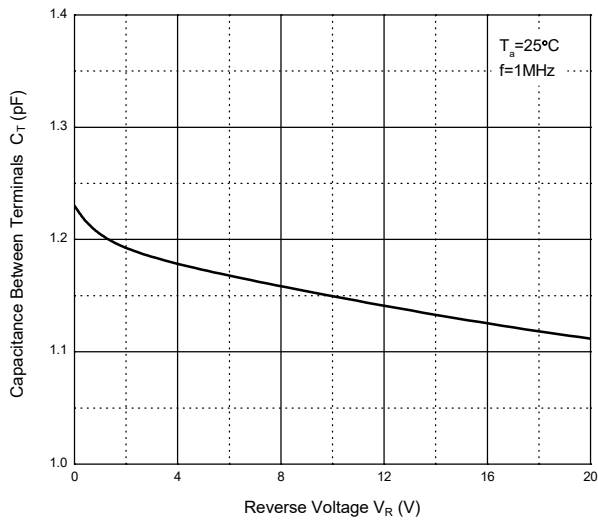
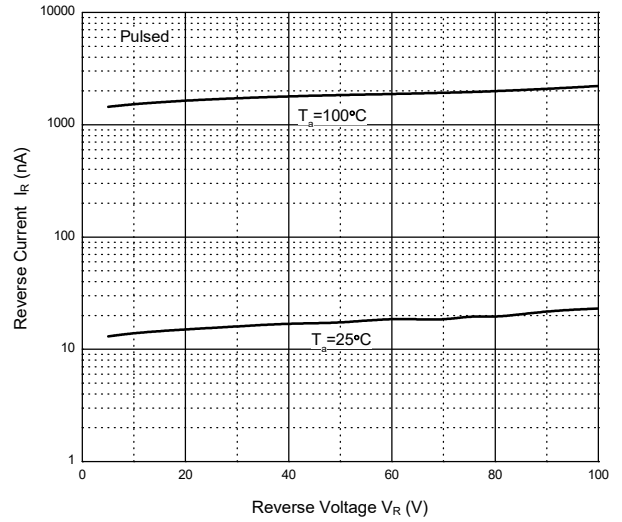
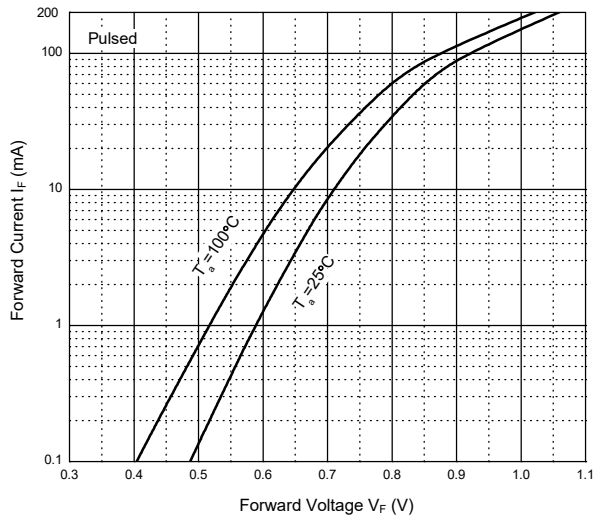
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$	V_F	0.55 0.67 0.75	0.7 0.82 1.1	V
Reverse Breakdown Voltage at $I_R = 100\ \mu\text{A}$	$V_{(BR)R}$	100	--	V
Reverse Current at $V_R = 50\text{ V}$ at $V_R = 100\text{ V}$	I_R	-- --	1 3	nA
Typical Junction Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_j	--	2	pF
Maximum Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$, $I_{RR} = 1\text{ mA}$, $R_L = 100\ \Omega$	T_{rr}	--	4	nS



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Typical Characteristic Curves





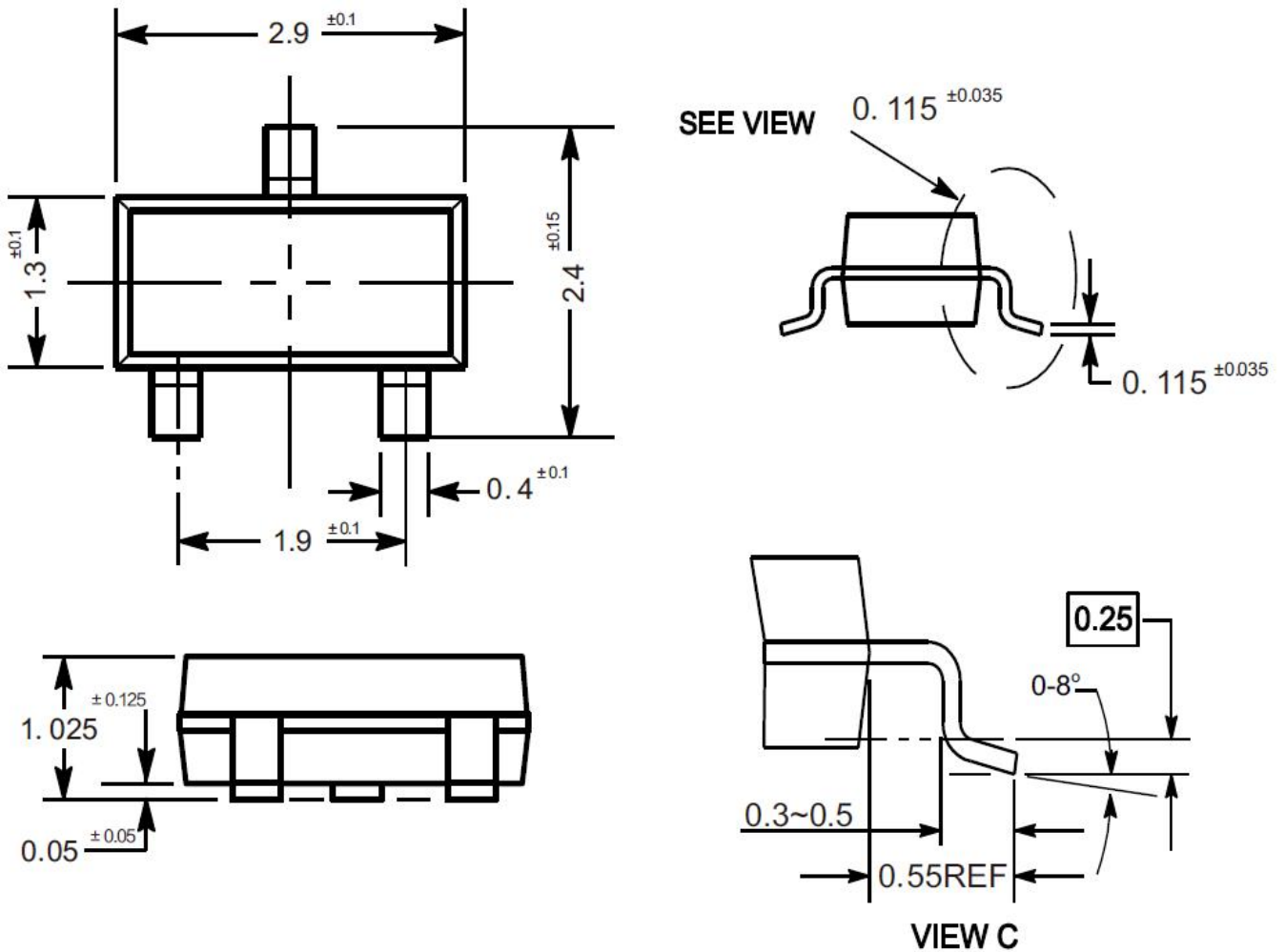
MMBD7000[†]

Silicon Epitaxial Planar Switching Diode

Package Outline

SOT-23

Dimensions in mm



Ordering Information

Device	Package	Shipping
MMBD7000	SOT-23	3,000PCS/Reel&7inches